Accepted Manuscript

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PII: S0925-8388(18)30187-7

DOI: 10.1016/j.jallcom.2018.01.186

Reference: JALCOM 44650

To appear in: Journal of Alloys and Compounds

Received Date: 23 November 2017

Revised Date: 12 January 2018

Accepted Date: 13 January 2018

Please cite this article as: J.-h. Chen, J. Ma, Y.-j. Zhang, L. Wu, C.W. Nan, Magnetic phase transition and large room temperature magnetoresistance in Ni doped FeRh films, *Journal of Alloys and Compounds* (2018), doi: 10.1016/j.jallcom.2018.01.186.

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ACCEPTED MANUSCRIPT

Magnetic phase transition and large room temperature magnetoresistance in Ni doped FeRh films

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Abstract

We have investigated the structural, magnetic and electrical transport properties of the Ni doped FeRh films prepared by magnetron co-sputtering. A large magetoresistance of 35%, induced by a reversible antiferromagnetic to ferromagnetic phase transition, is obtained at room temperature with only 1 mol.% Ni addition. Magnetic field is revealed to have an equivalent effect as temperature to drive the magnetic phase transition. Moreover, the way to realize a nonvolatile room temperature magetoresistance effect is also discussed. These results give FeRh the possibility of technological application in the spintronic field at room temperature, which are referential to other material systems with a first-order magnetic phase transition.

Key Words: FeRh, magnetic transition, doping, magnetoresistance, room temperature

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